

SMD Schottky Barrier Diode

Comchip
SMD Diode Specialist

CDBT0540-G

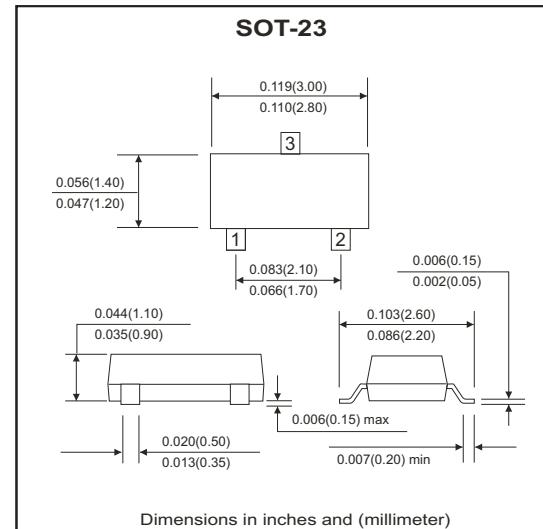
RoHS Device



Features

- Small surface mount type.
- Low reverse current and low forward voltage.
- High reliability.

Marking: D3A



Maximum Ratings (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	V _R	40	V
Peak surge forward voltage	I _{FSM}	3	A
Mean rectifying current	I _o	0.5	A
Power dissipation	P _D	250	mW
Thermal resistance, junction to ambient	R _{θJA}	500	°C/W
Junction temperature	T _J	125	°C
Storage temperature	T _{STG}	-40 to +125	°C

Electrical Characteristics (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ.	Max	Unit
Reverse breakdown voltage	V _{BR}	I _R =100µA	40			V
Forward voltage	V _F	I _F =500mA			0.55	V
Reverse current	I _R	V _R =10V			30	µA
		V _R =30V			50	µA
Capacitance between terminals	C _T	V _R =0V, f=1MHz		125		pF
		V _R =10V, f=1MHz		20		pF

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RATING AND CHARACTERISTIC CURVES (CDBT0540-G)

Fig.1 Forward Characteristics

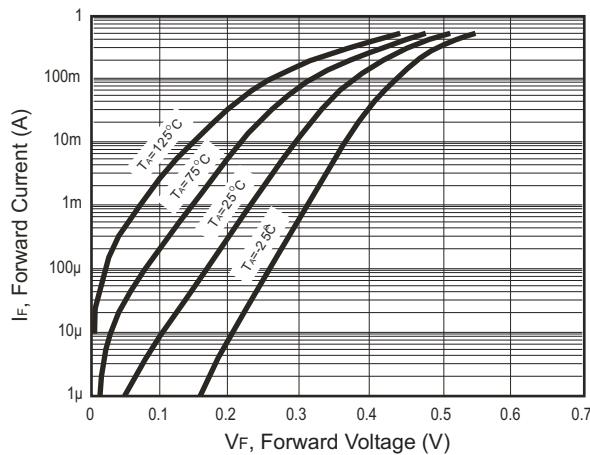


Fig.2 Reverse Characteristics

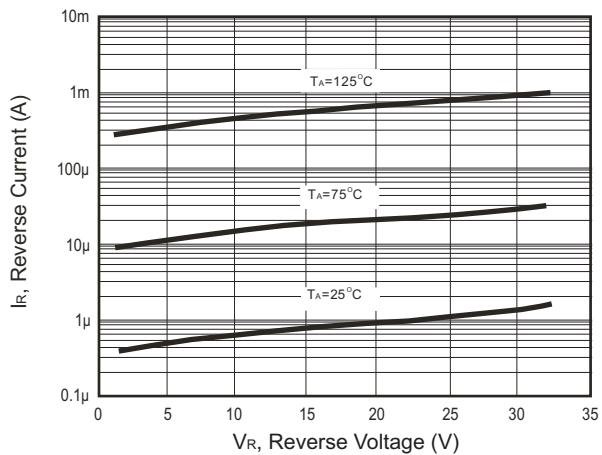


Fig.3 Capacitance Between Terminals Characteristics

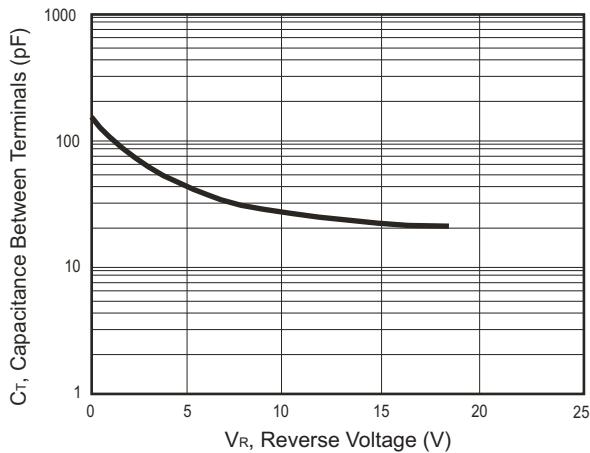


Fig.4 Power Derating Curve

